DEVICE HAVING A CONTACT BETWEEN SEMICONDUCTOR REGIONS THROUGH A BURIED INSULATING LAYER, AND PROCESS FOR FABRICATING SAID DEVICE

ABSTRACT

According to a first aspect, the invention relates to a semiconductor device produced on a semiconductor-on-insulator substrate comprising a thin layer (1) of semiconductor material separated from a base substrate (2) by means of a buried insulating layer (3, BOX), the device comprising a first conducting region (4, D1, S, E) in the thin layer and a second conducting region (5, BL, SL, IL) in the base substrate and being characterized by a contact (I1, I2, I_N, I_P) connecting the first region to the second region through the insulating layer.

According to a second aspect, the invention relates to a process for fabricating a semiconductor device according to its first aspect.

Fig. 1